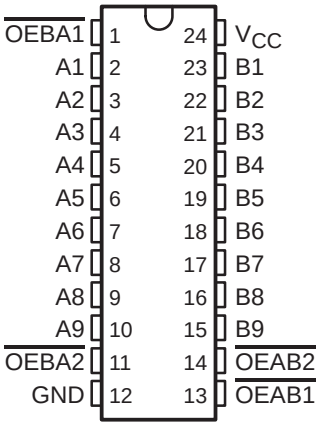
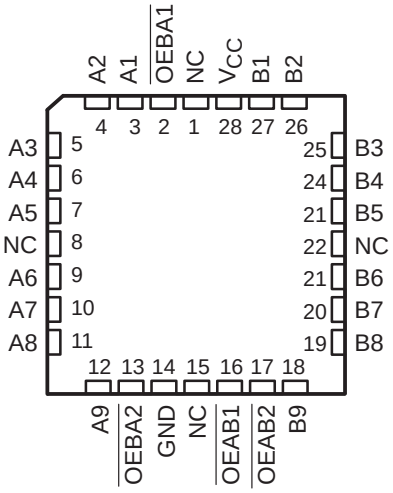
- **State-of-the-Art *EPIC*-II*B*™ BiCMOS Design Significantly Reduces Power Dissipation**
- **Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C**
- **High-Impedance State During Power Up and Power Down**
- **High-Drive Outputs (–32-mA I_{OH}, 64-mA I_{OL})**
- **Latch-Up Performance Exceeds 500 mA Per JESD 17**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB) Packages, and Thin Shrink Small-Outline (PW), Ceramic Chip Carriers (FK), Plastic (NT), and Ceramic (JT) DIPs**

SN54ABT863 . . . JT PACKAGE
SN74ABT863 . . . DB, DW, NT, OR PW PACKAGE
(TOP VIEW)



SN54ABT863 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

The ’ABT863 devices are 9-bit transceivers designed for asynchronous communication between data buses. The control-function implementation allows for maximum flexibility in timing.

These devices allow noninverted data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic levels at the output-enable ($\overline{OEAB}$ and $\overline{OEBA}$) inputs.

The outputs are in the high-impedance state during power up and power down. The outputs remain in the high-impedance state while the device is powered down.

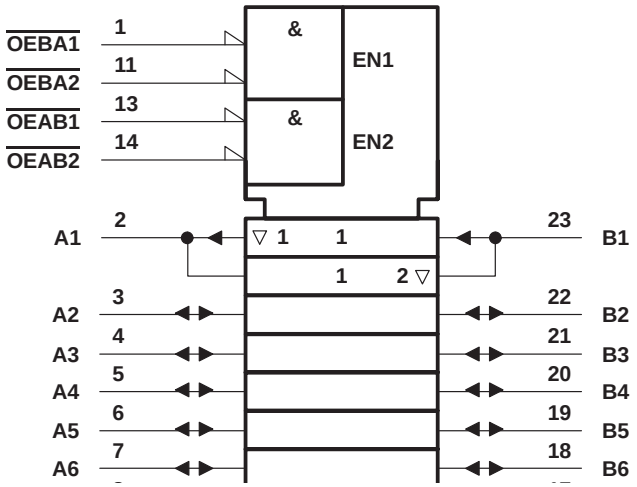
When V_{CC} is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54ABT863 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT863 is characterized for operation from –40°C to 85°C.

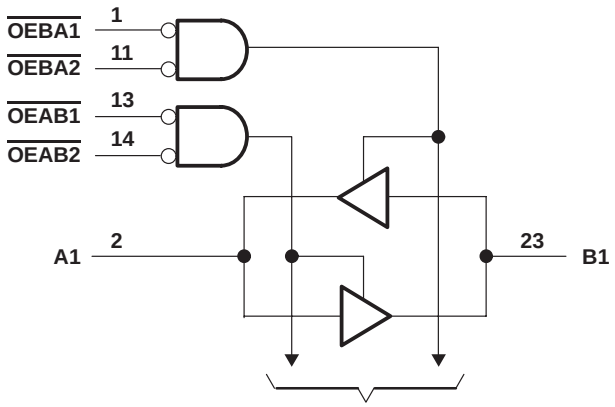
FUNCTION TABLE

INPUTS				OPERATION
$\overline{OEAB1}$	$\overline{OEAB2}$	$\overline{OEBA1}$	$\overline{OEBA2}$	
L	L	L	L	Latch A and B
L	L	H	X	A to B
L	L	X	H	
H	X	L	L	B to A
X	H	L	L	
H	X	H	X	Isolation
H	X	X	H	
X	H	X	H	
X	H	H	X	

logic symbol†



logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, NT, and PW packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (except I/O ports) (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O . . . . . –0.5 V to 5.5 V
Current into any output in the low state, I_O: SN54ABT863 . . . . . 96 mA
SN74ABT863 . . . . . 128 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –18 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package . . . . . 104°C/W
DW package . . . . . 81°C/W
NT package . . . . . 67°C/W
PW package . . . . . 120°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

			SN54ABT863		SN74ABT863		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		5		5	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

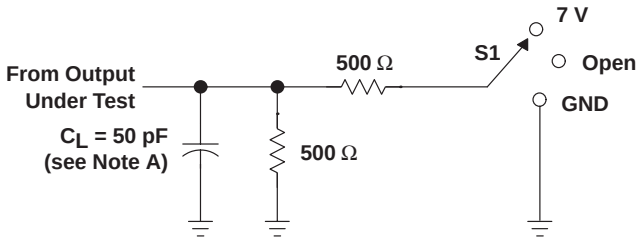
PARAMETER		TEST CONDITIONS		T_A = 25°C			SN54ABT863		SN74ABT863		UNIT
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = –18 mA			–1.2		–1.2		–1.2	V
V_{OH}		V_{CC} = 4.5 V,	I_{OH} = –3 mA	2.5			2.5		2.5		V
		V_{CC} = 5 V,	I_{OH} = –3 mA	3			3		3		
		V_{CC} = 4.5 V	I_{OH} = –24 mA	2			2				
			I_{OH} = –32 mA	2*					2		
V_{OL}		V_{CC} = 4.5 V	I_{OL} = 48 mA			0.55		0.55			V
			I_{OL} = 64 mA			0.55*				0.55	
V_{hys}					100						mV
I_I	Control inputs	V_{CC} = 0 to 5.5 V,	V_I = V_{CC} or GND			±1		±1		±1	µA
	A or B ports	V_{CC} = 2.1 V to 5.5 V,	V_I = V_{CC} or GND			±20		±20		±20	
I_{OZPU}		V_{CC} = 0 to 2.1 V, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = * don't care				±50		±50**		±50	µA
I_{OZPD}		V_{CC} = 2.1 V to 0, V_O = 0.5 V to 2.7 V, $\overline{OE}$ = * don't care				±50		±50**		±50	µA
I_{OZH}‡		V_{CC} = 2.1 V to 5.5 V, V_O = 2.7 V, $\overline{OE}$ ≥ 2 V				10		10		10	µA
I_{OZL}‡		V_{CC} = 2.1 V to 5.5 V, V_O = 0.5 V, $\overline{OE}$ ≥ 2 V				–10		–10		–10	µA
I_{off}		V_{CC} = 0,	V_I or V_O ≤ 4.5 V			±100*				±100	µA
I_{CEX}		V_{CC} = 5.5 V, V_O = 5.5 V	Outputs high			50		50		50	µA
I_O§		V_{CC} = 5.5 V,	V_O = 2.5 V	–50	–100	–225	–50	–225	–50	–225	mA
I_{CC}	A or B ports	V_{CC} = 5.5 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		1	250		250		250	µA
			Outputs low		24	30		38		38	mA
			Outputs disabled		0.5	250		250		250	µA
ΔI_{CC}¶	Data inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND	Outputs enabled			1.5		1.5		1.5	mA
			Outputs disabled			0.05		0.05		0.05	
	Control inputs	V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND				1.5		1.5		1.5	
C_i	Control inputs	V_I = 2.5 V or 0.5 V			4						pF
C_{io}	A or B ports	V_O = 2.5 V or 0.5 V			7						pF

* On products compliant to MIL-PRF-38535, this parameter does not apply.
** On products compliant to MIL-PRF-38535, this parameter is not production tested.
† All typical values are at V_{CC} = 5 V.
‡ The parameters I_{OZH} and I_{OZL} include the input leakage current.
§ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

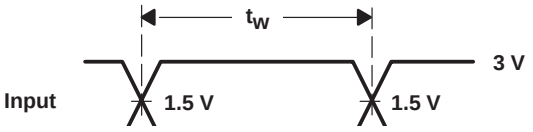
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 5 V, T_A = 25°C			SN54ABT863		SN74ABT863		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1	2.6	4.1	1	7	1	5.7	ns
t_{PHL}			1	2.3	3.3	1	3.9	1	3.9	
t_{PZH}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	1	3.2	4.3	1	5.4	1	5.5	ns
t_{PZL}			1	3.3	4.4	1	5.5	1	5.4	
t_{PHZ}	$\overline{OEAB}$ or $\overline{OEBA}$	B or A	2.5	4.8	6	2.5	6.8	2.5	6.7	ns
t_{PLZ}			1.5	4.4	5.9	1.5	7.8	1.5	6.9	

PARAMETER MEASUREMENT INFORMATION



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open



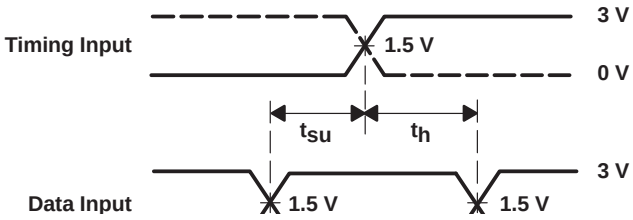


Figure 1. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74ABT863DW	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT863
SN74ABT863DW.B	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT863
SN74ABT863DWR	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT863
SN74ABT863DWR.B	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	ABT863

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

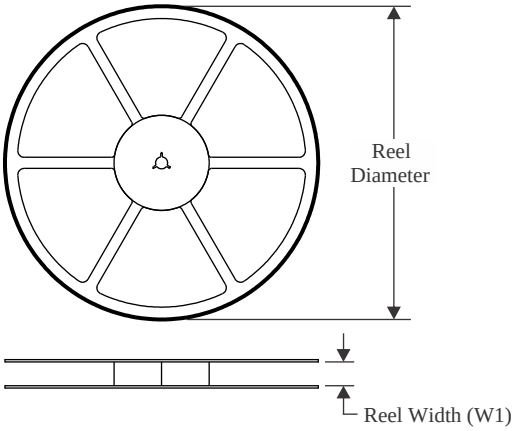
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

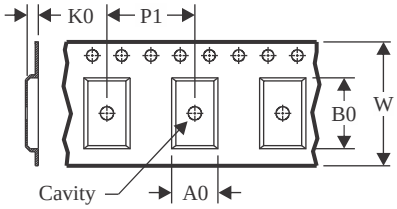
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

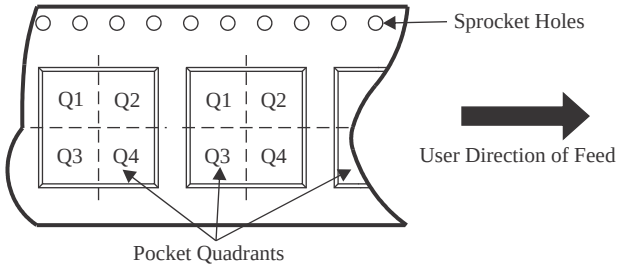


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

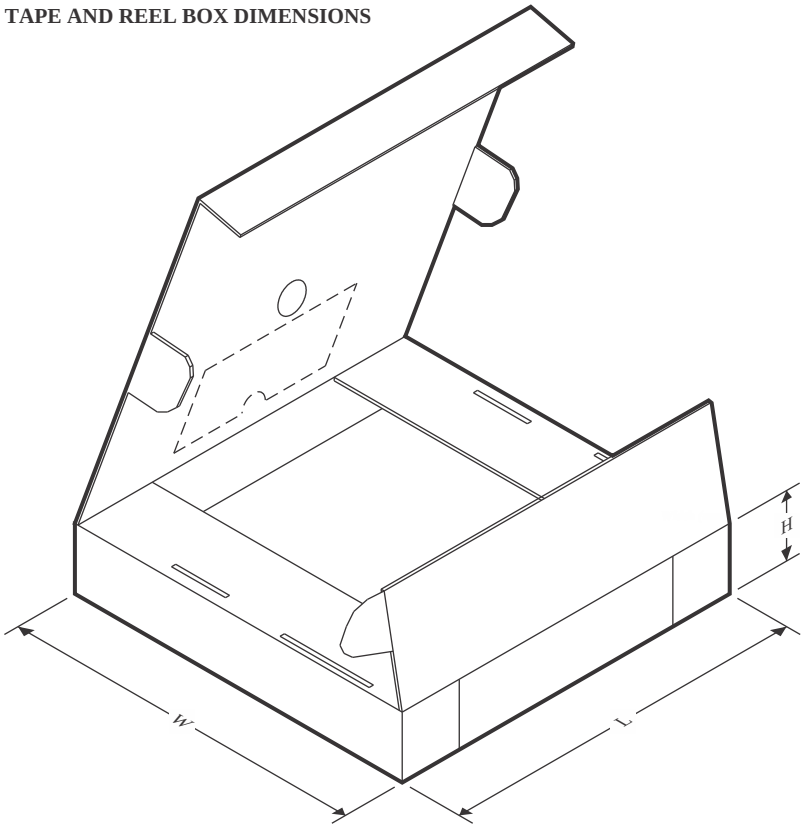
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74ABT863DWR	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1

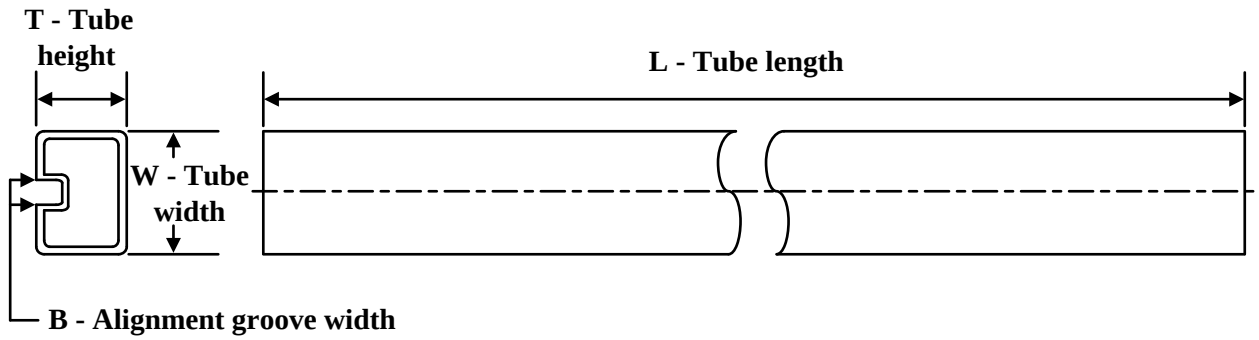
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74ABT863DWR	SOIC	DW	24	2000	350.0	350.0	43.0

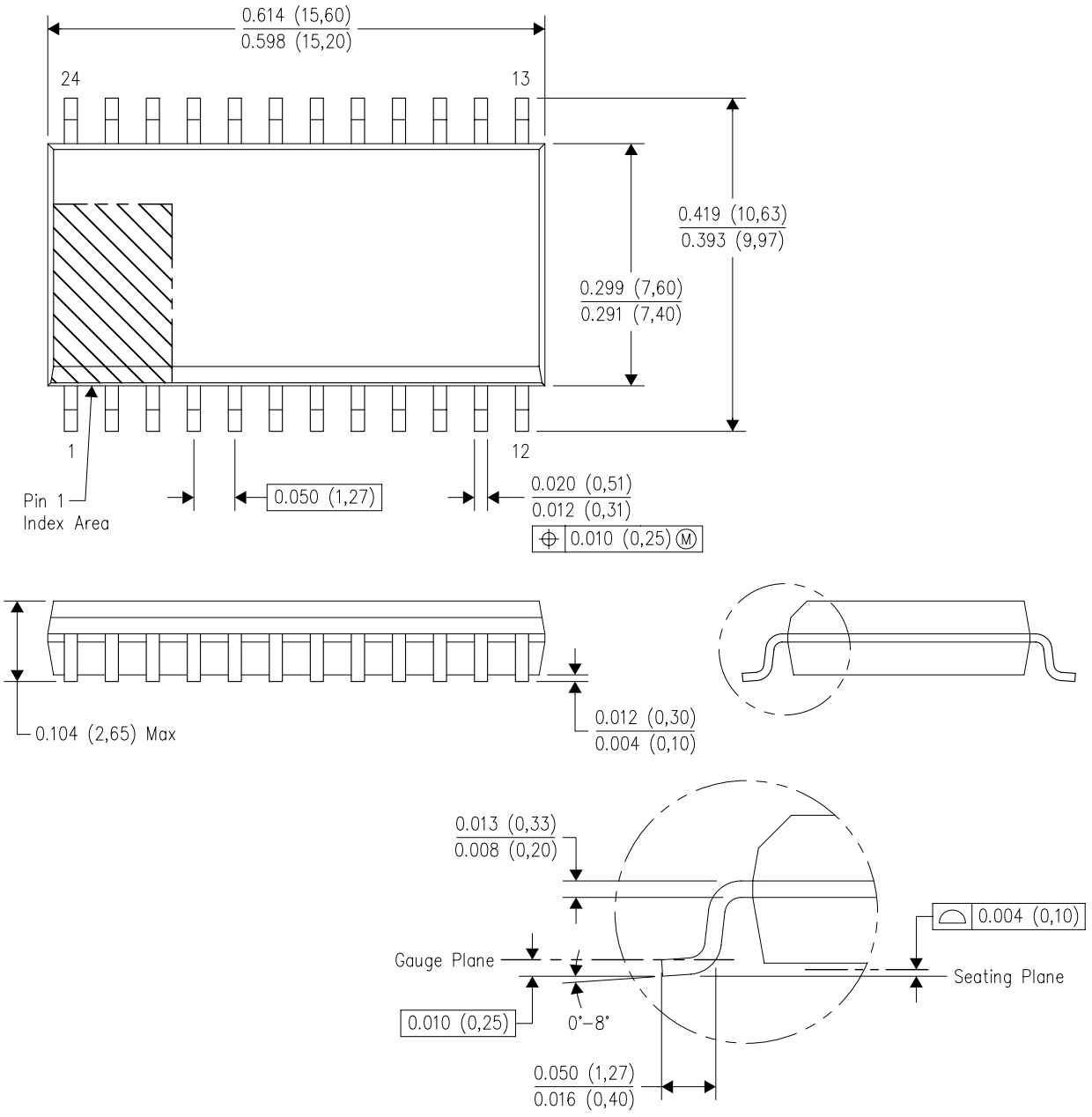
TUBE



*All dimensions are nominal

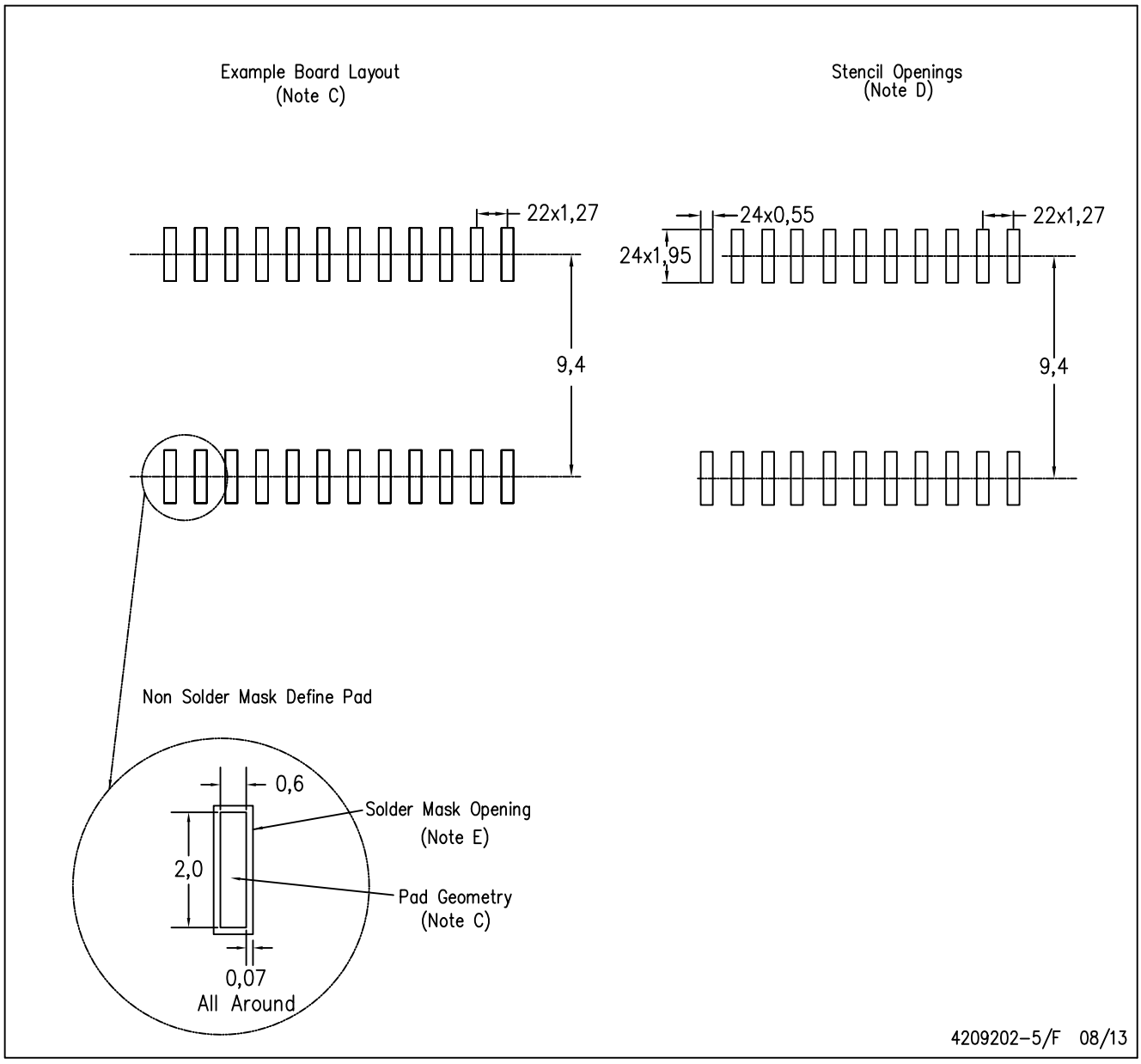
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74ABT863DW	DW	SOIC	24	25	506.98	12.7	4826	6.6
SN74ABT863DW.B	DW	SOIC	24	25	506.98	12.7	4826	6.6

DW (R–PDSO–G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AD.

DW (R–PDSO–G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Refer to IPC7351 for alternate board design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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